## 100V P-CHANNEL ENHANCEMENT MODE MOSFET

#### **SUMMARY**

 $V_{(BR)DSS}$  = - 100V :  $R_{DS}(_{on})$  = 0.150 $\Omega$  ;  $I_{D}$  = - 3.7A

#### **DESCRIPTION**

This new generation of Trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

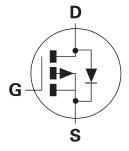


FEATURES SOT223

- · Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package

### **APPLICATIONS**

- DC-DC Converters
- Power Management functions
- Relay and Solenoid driving
- Motor control



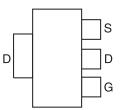
#### **ORDERING INFORMATION**

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL	
ZXMP10A18GTA	7″	12mm	1,000 units	
ZXMP10A18GTC	13"	12mm	4,000 units	

# **DEVICE MARKING**

 ZXMP 10A18

## **PINOUT**





## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	-100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current @ V <sub>GS</sub> =10V; T <sub>A</sub> =25°C (b)	I <sub>D</sub>	-3.7	А
@V <sub>GS</sub> =10V; T <sub>A</sub> =70°C <sup>(b)</sup>		-3.0	А
@ V <sub>GS</sub> =10V; T <sub>A</sub> =25°C <sup>(a)</sup>		-2.6	А
Pulsed Drain Current <sup>(c)</sup>	I <sub>DM</sub>	-16.5	Α
Continuous Source Current (Body Diode) (b)	I <sub>S</sub>	-5.3	А
Pulsed Source Current (Body Diode) (c)	I <sub>SM</sub>	-16.5	А
Power Dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	2	W
Linear Derating Factor		16	mW/°C
Power Dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	3.9	W
Linear Derating Factor		31	mW/°C
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient <sup>(a)</sup>	$R_{\Theta JA}$	62.5	°C/W
Junction to Ambient <sup>(b)</sup>	$R_{\Theta JA}$	32.2	°C/W

## NOTES

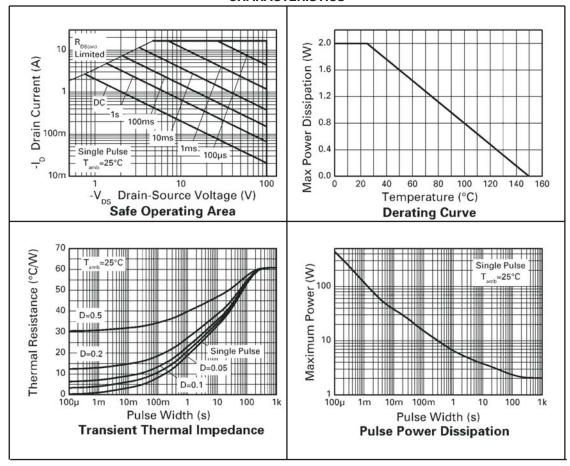
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.



<sup>(</sup>b) For a device surface mounted on FR4 PCB measured at t  $\leq$  10 sec.

<sup>(</sup>c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02 pulse width =  $300 \mu s$  - pulse width limited by maximum junction temperature.

## **CHARACTERISTICS**



**ZETEX** 

# **ELECTRICAL CHARACTERISTICS** (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

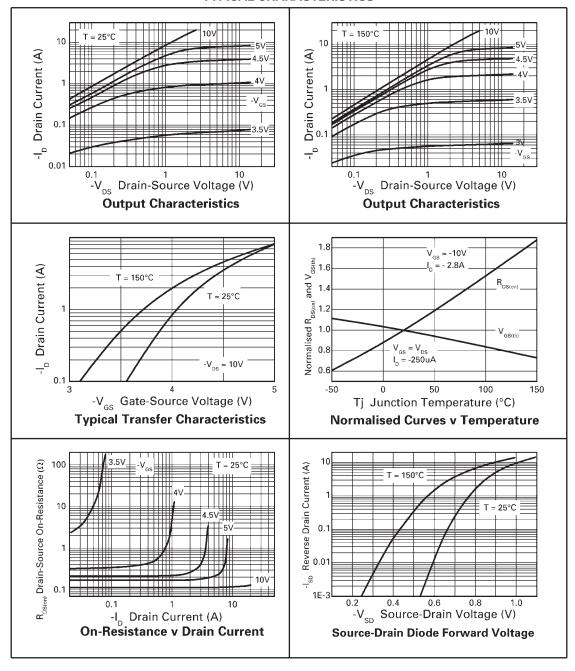
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
STATIC		•					
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	-100			V	I <sub>D</sub> = -250μA, V <sub>GS</sub> =0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1	μΑ	V <sub>DS</sub> = -100V, V <sub>GS</sub> =0V	
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	-2.0		-4.0	V	I <sub>D</sub> = -250μA, V <sub>DS</sub> =V <sub>GS</sub>	
Static Drain-Source On-State	R <sub>DS(on)</sub>			0.150	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.8A	
Resistance (1)				0.190	Ω	$V_{GS} = -6V, I_{D} = -2.4A$	
Forward Transconductance (1)(3)	g <sub>fs</sub>		6.0		S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.8A	
DYNAMIC (3)	·	•					
Input Capacitance	C <sub>iss</sub>		1055		pF		
Output Capacitance	C <sub>oss</sub>		90		pF	V <sub>DS</sub> = -50V, V <sub>GS</sub> =0V	
Reverse Transfer Capacitance	C <sub>rss</sub>		76		pF	f=1MHz	
SWITCHING (2) (3)		•			•		
Turn-On Delay Time	t <sub>d(on)</sub>		4.6		ns		
Rise Time	t <sub>r</sub>		6.8		ns	V <sub>DD</sub> = -50V, I <sub>D</sub> = -1A	
Turn-Off Delay Time	t <sub>d(off)</sub>		33.9		ns	$R_{G} = 6.0\Omega, V_{GS} = -10V$	
Fall Time	t <sub>f</sub>		17.9		ns	1.0 2.2.2, 1.03	
Total Gate Charge	Qg		26.9		nC	V <sub>DS</sub> = -50V, V <sub>GS</sub> = -10V	
Gate-Source Charge	Q <sub>gs</sub>		3.9		nC	$I_{DS} = -30V, V_{GS} = -10V$	
Gate-Drain Charge	Q <sub>gd</sub>		10.2		nC	102.07	
SOURCE-DRAIN DIODE	, -	•			•	,	
Diode Forward Voltage (1)	V <sub>SD</sub>		-0.85	-0.95	V	T <sub>j</sub> =25°C, I <sub>S</sub> = -3.5A,	
						V <sub>GS</sub> =0V	
Reverse Recovery Time (3)	t <sub>rr</sub>		49		ns	T <sub>j</sub> =25°C, I <sub>S</sub> = -2.8A,	
Reverse Recovery Charge (3)	Q <sub>rr</sub>		107		nC	di/dt=100A/μs	

#### **NOTES**

- (1) Measured under pulsed conditions. Pulse width  $\leq$  300ms; duty cycle  $\leq$  2%.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

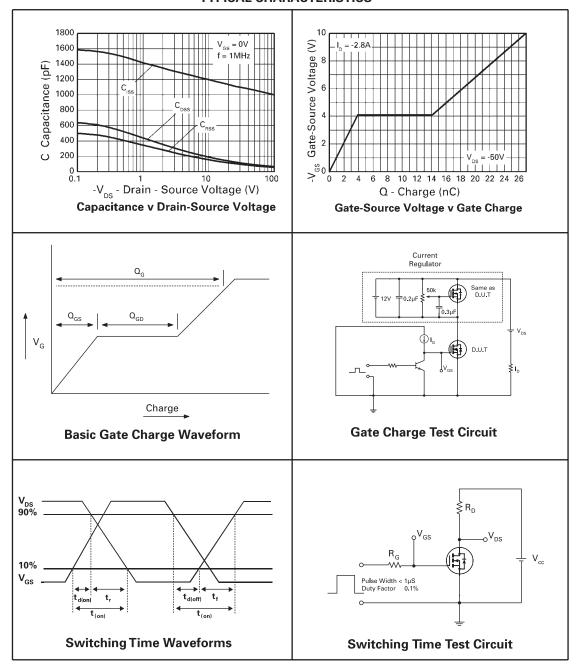


### **TYPICAL CHARACTERISTICS**





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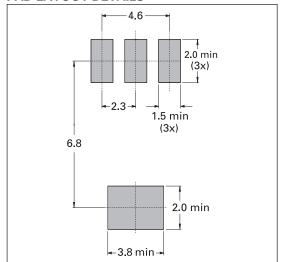




## **PACKAGE OUTLINE**

# A C C E K K G G G

## **PAD LAYOUT DETAILS**



Controlling dimensions are in millimetres. Approximate conversions are given in inches

## **PACKAGE DIMENSIONS**

DIM	Millin	netres	Inc	hes	DIM	Millimetres		Inches	
DIIVI	Min	Max	Min	Max	ואווט	Min	Max	Min	Max
А	6.3	6.7	0.248	0.264	G	NON	1 4.6	NOM	0.181
В	3.3	3.7	0.130	0.146	Н	0.85	1.05	0.033	0.041
С	-	1.7	-	0.067	K	0.02	0.10	0.0008	0.004
D	0.6	0.8	0.024	0.031	L	6.7	7.3	0.264	0.287
Е	2.9	3.1	0.114	0.122	М	NON	1 2.3	NOM	0.0905
F	0.24	0.32	0.009	0.13					

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